NIKO-SEM

N-Channel Enhancement Mode Field Effect Transistor

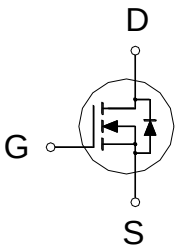
PB600BA

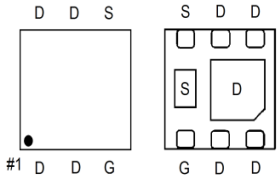
PDFN 2x2S

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	12mΩ	9A





G : GATE
D : DRAIN
S : SOURCE

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A = 25 °C	I_D	9	A
	T_A = 70 °C		7.2	
Pulsed Drain Current[1]		I_{DM}	27	
Avalanche Current		I_{AS}	12.6	
Avalanche Energy	L = 0.1mH	E_{AS}	7.9	mJ
Power Dissipation	T_A = 25 °C	P_D	1.7	W
	T_A = 70 °C		1.1	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	$R_{\theta JA}$		71.7	°C／W

[1]Pulse width limited by maximum junction temperature.
[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Coppe.

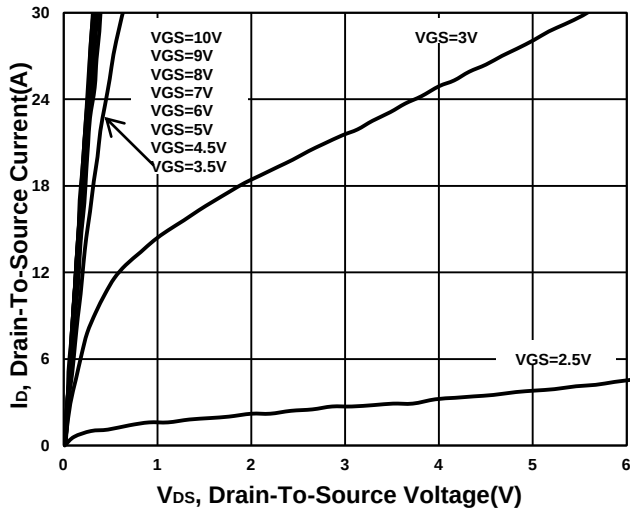
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.3	1.7	2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V			1	μA
		V_{DS} = 20V, V_{GS} = 0V, T_J = 55 °C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 9A		11	17.5	mΩ
		V_{GS} = 10V, I_D = 9A		9	12	
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 9A		45		S

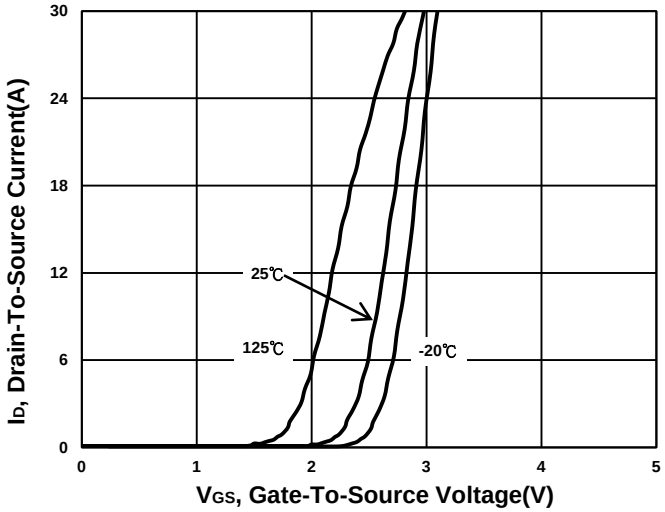
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		706		pF
Output Capacitance	C_{oss}			103		
Reverse Transfer Capacitance	C_{rss}			74		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		3.1		Ω
Total Gate Charge[2]	$Q_{g(V_{GS}=10V)}$	V_{DS} = 15V , I_D = 9A		15		nC
	$Q_{g(V_{GS}=4.5V)}$			8		
Gate-Source Charge[2]	Q_{gs}			2.6		
Gate-Drain Charge[2]	Q_{gd}			3.6		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 15V $I_D \cong$ 9A, V_{GEN} = 10V, R_G = 6Ω		13		nS
Rise Time[2]	t_r			37		
Turn-Off Delay Time[2]	$t_{d(off)}$			48		
Fall Time[2]	t_f			25		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				1.5	A
Forward Voltage[1]	V_{SD}	I_F = 9A, V_{GS} = 0V			1.1	V
Reverse Recovery Time	t_{rr}	I_F = 9A , dI_F/dt = 100A / μS		11		nS
Reverse Recovery Charge	Q_{rr}			3		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

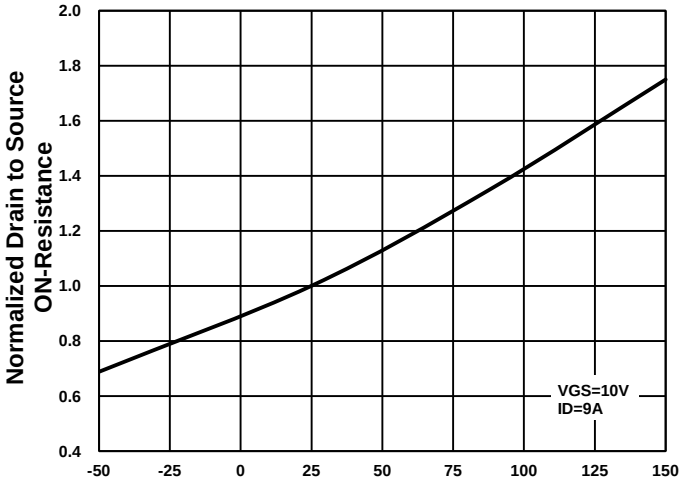
Output Characteristics



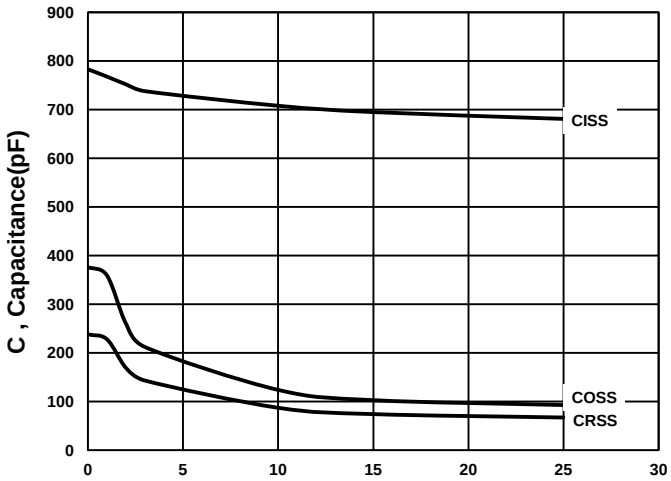
Transfer Characteristics



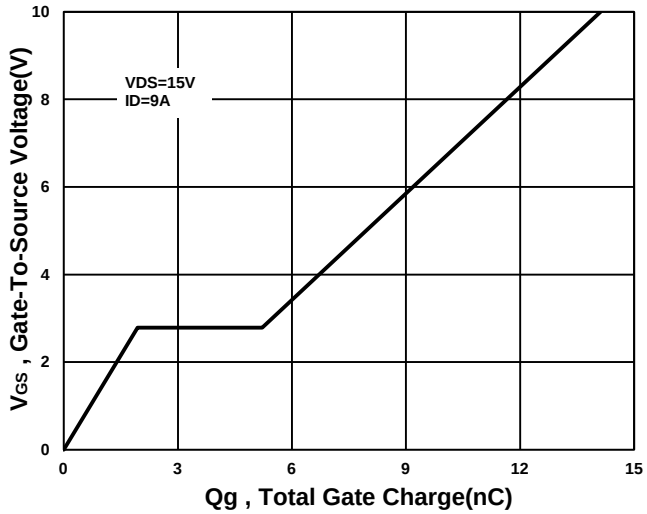
On-Resistance VS Temperature



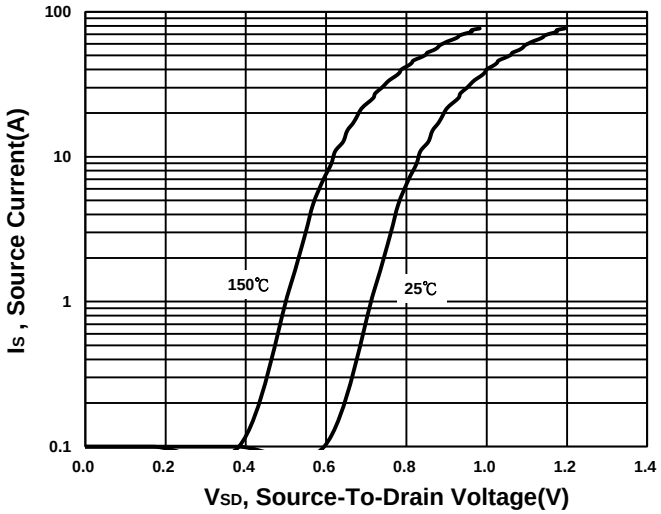
Capacitance Characteristic



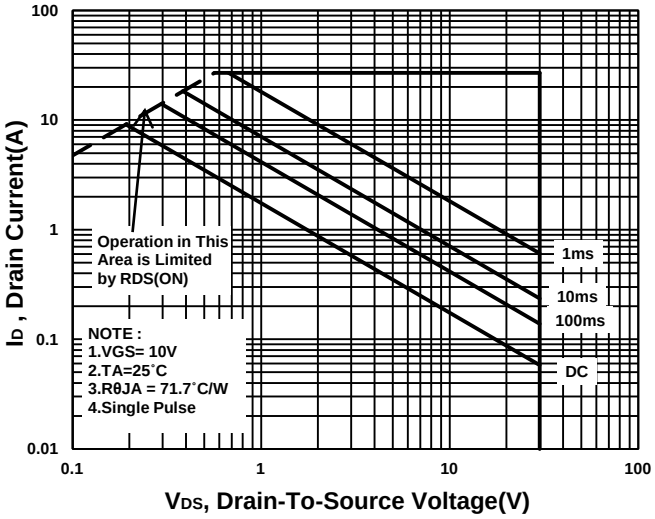
Gate charge Characteristics



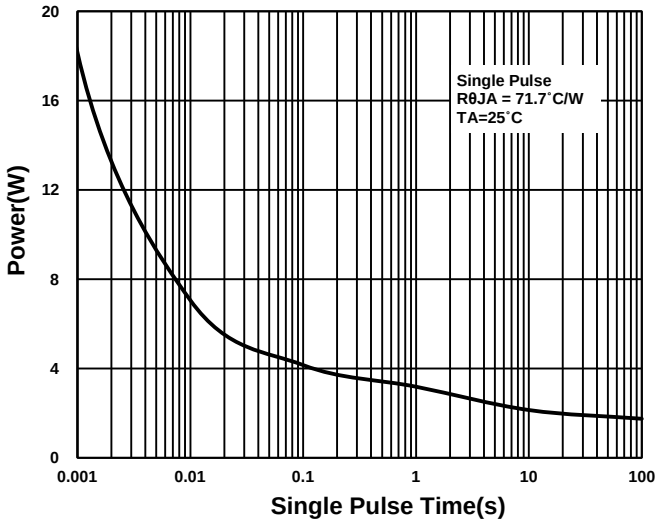
Source-Drain Diode Forward Voltage



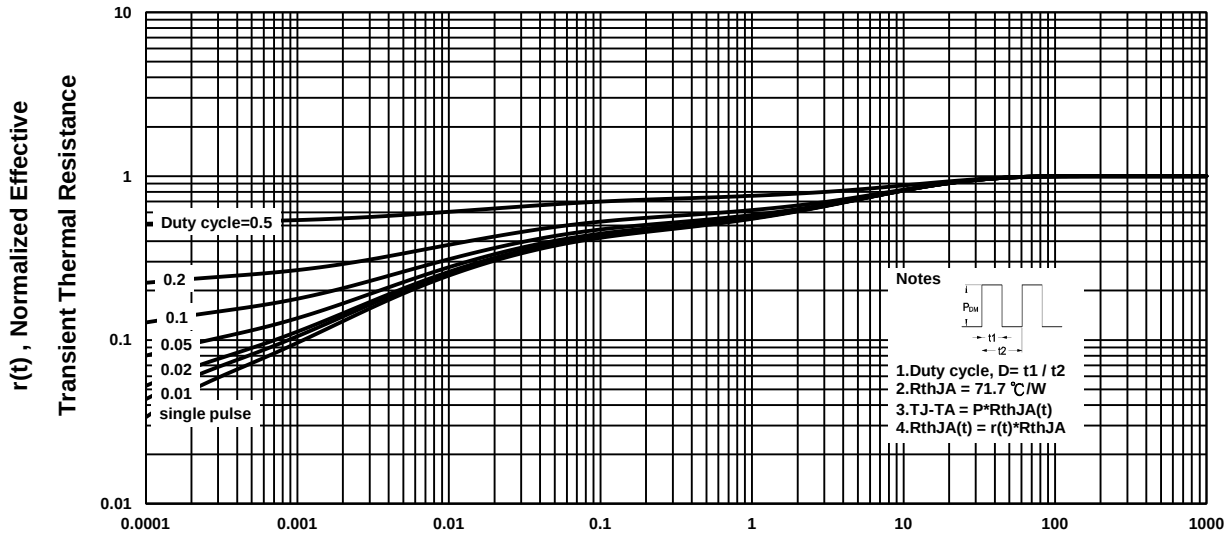
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



T1 , Square Wave Pulse Duration[sec]